

isc Silicon NPN Power Transistor

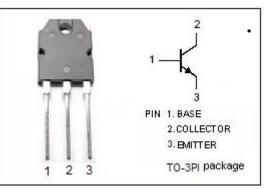
2SC3376

DESCRIPTION

- Collector-Emiiter Breakdown Voltage-
- : V_{(BR)CEO}= 800V(Min.) • High Speed Switching
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Switching regulator and high voltage switching applications.
- High speed DC-DC converter applications.



ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

				- I - O	0	1	0.50
SYMBOL	PARAMETER	VALUE	UNIT	Î.P.	¢	ż E	₽¥
V _{CBO}	Collector-Base Voltage	900	V			* <	Ly I
V _{CEO}	Collector-Emitter Voltage	800	V	к - ж.			
V _{EBO}	Emitter-Base Voltage	7	V		Ļ	→ R	-J ■
lc	Collector Current-Continuous	3	A			m	200
IC.		5			DIM	MIN 19.90	MAX 20.10
	Collector Current-Peak			-	B	15.50	15.70
I _{CM}		5	A		C	4.40	4.60
					D	0.90	1.10
	Base Current-Continuous	1	А		F	3.20	3.4
IB					H	2.90	3.10
				-	J	0.50	0.7
_	Collector Power Dissipation @Tc=25°C	60	W		K	19.90 1.90	20.10
Pc					N	10.80	11.0
				-	Q	4.40	4.60
т	Junction Temperature	150	°C		R	3.30	3.3
Tj					S	1.40	1.60
				-	Т	1.00	1.20
T _{stg}	Storage Temperature Range	-55~150	°C		U	2.10	2.30
					Z	8.90	9.10

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isc website: www.iscsemi.com

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ELECTRICAL CHARACTERISTICS

$T_{c}\text{=}25\,^{\circ}\!\!\!\!^{\circ}\!\!\!^{\circ}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA; I _B = 0	800			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 1mA; I _E = 0	900			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 0.8A; I _B = 0.16A			0.6	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 0.8A; I _B = 0.16A			1.2	V
Ісво	Collector Cutoff Current	V _{CB} = 800V; I _E = 0			0.1	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 7V; I _C = 0			1.0	mA
h _{FE}	DC Current Gain	I _C = 0.8A; V _{CE} = 5V	10			

Switching Times; Resistive Load

tr	Rise Time			1.0	μ S
ts	Storage Time	I _{B1} = 0.08A; I _{B2} = -0.2A; V _{CC} ≈ 400V; R _L = 500 Ω		4.0	μ S
t _f	Fall Time			1.0	μ S

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